# Quad Analog Switch/ Multiplexer/Demultiplexer with Separate Analog and Digital Power Supplies

# **High-Performance Silicon-Gate CMOS**

The MC74HC4316A utilizes silicon-gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF-channel leakage current. This bilateral switch/multiplexer/demultiplexer controls analog and digital voltages that may vary across the full analog power-supply range (from  $V_{CC}$  to  $V_{EE}$ ).

The HC4316A is similar in function to the metal-gate CMOS MC14016 and MC14066, and to the High-Speed CMOS HC4066A. Each device has four independent switches. The device control and Enable inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs. The device has been designed so that the ON resistances ( $R_{\rm ON}$ ) are much more linear over input voltage than  $R_{\rm ON}$  of metal-gate CMOS analog switches. Logic-level translators are provided so that the On/Off Control and Enable logic-level voltages need only be  $V_{\rm CC}$  and  $V_{\rm CC}$  and  $V_{\rm CC}$  while the switch is passing signals ranging between  $V_{\rm CC}$  and  $V_{\rm CC}$ . When the Enable pin (active-lew) is high, all out and log stritches are turned off.

# **Features**

- Logic-Level Translator for On/Off Control and Enable Inputs
- Fast Switching and Propagation Speeds
- High ON/OFF Output Voltage Ratio
- Diode Protection on All Inputs/Outputs
- Analog Power-Supply Voltage Range  $(V_{CC} V_{EE}) = 2.0$  to 12.0 V
- Digital (Control) Power-Supply Voltage Range (V<sub>CC</sub> - GND) = 2.0 V to 6.0 V, Independent of V<sub>EE</sub>
- Improved Linearity of ON Resistance
- Chip Complexity: 66 FETs or 16.5 Equivalent Gates
- Pb-Free Packages are Available\*



# ON Semiconductor®

http://onsemi.com

# MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B







A = Assembly Location

WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC4316AN	PDIP-16	500 Units / Box
MC74HC4316ANG	PDIP-16 (Pb-Free)	500 Units / Box
MC74HC4316ADR2	SOIC-16	2500/Tape&Reel
MC74HC4316ADR2G	SOIC-16 (Pb-Free)	2500/Tape&Reel
MC74HC4316AFEL	SOEIAJ-16	50/Tape&Reel
MC74HC4316AFELG	SOEIAJ-16 (Pb-Free)	50/Tape&Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

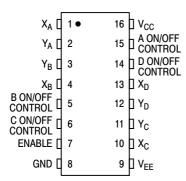


Figure 1. Pin Assignment

## **FUNCTION TABLE**

Inpu	State of Analog	
Enable	On/Off Control	Switch
L L H	H L X	On Off Off

X = Don't Care.

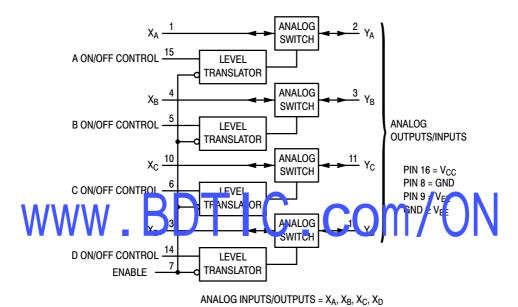


Figure 2. Logic Diagram

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage (Ref. to GND) (Ref. to $V_{\text{EE}}$ )	- 0.5 to + 7.0 - 0.5 to + 14.0	V
V <sub>EE</sub>	Negative DC Supply Voltage (Ref. to GND)	- 7.0 to + 0.5	V
V <sub>IS</sub>	Analog Input Voltage	V <sub>EE</sub> – 0.5 to V <sub>CC</sub> + 0.5	<b>V</b>
V <sub>in</sub>	DC Input Voltage (Ref. to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I	DC Current Into or Out of Any Pin	± 25	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP* EIAJ/SOIC Package* TSSOP Package*	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{\rm CC}$ ). Unused outputs must be left open. I/O pins must be connected to a properly terminated line or bus.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

EIAJ/SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit		, ,
V <sub>CC</sub>	Positive CC Sur bly Vota je (Ref. to GN ))		2.0	6.0		m	/ (
V <sub>EE</sub>	Negative CD Supply of age (Ret to all D)		- 0	GNL	Y		
V <sub>IS</sub>	Analog Input Voltage		V <sub>EE</sub>	V <sub>CC</sub>	V		
V <sub>in</sub>	Digital Input Voltage (Ref. to GND)		GND	V <sub>CC</sub>	V		
V <sub>IO</sub> *	Static or Dynamic Voltage Across Switch		-	1.2	V		
T <sub>A</sub>	Operating Temperature, All Package Types		<b>– 55</b>	+ 125	°C		
t <sub>r</sub> , t <sub>f</sub>	(Control or Enable Inputs) V <sub>CC</sub> = (Figure 10) V <sub>CC</sub> =	= 2.0 V = 3.0 V = 4.5 V = 6.0 V	0 0 0	1000 600 500 400	ns		

<sup>\*</sup>For voltage drops across the switch greater than 1.2 V (switch on), excessive  $V_{CC}$  current may be drawn; i.e., the current out of the switch may contain both  $V_{CC}$  and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC ELECTRICAL CHARACTERISTICS Digital Section (Voltages Referenced to GND) V<sub>EE</sub> = GND Except Where Noted

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Voltage, Control or Enable Inputs	R <sub>on</sub> = Per Spec	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Voltage, Control or Enable Inputs	R <sub>on</sub> = Per Spec	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	٧
l <sub>in</sub>	Maximum Input Leakage Current, Control or Enable Inputs	$V_{in} = V_{CC}$ or GND $V_{EE} = -6.0 \text{ V}$	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$\begin{aligned} V_{in} &= V_{CC} \text{ or GND} \\ V_{IO} &= 0 \text{ V} & V_{EE} &= GNE \\ V_{EE} &= -6.6 \end{aligned}$		2 4	20 40	40 160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# DC ELECTRICAL CHARACTERISTICS Analog Section (Voltages Referenced to V<sub>EE</sub>)

					Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	V <sub>EE</sub>	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
R <sub>on</sub>	Maximum "ON" Resistance	$V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ to $V_{EE}$ $I_{S} \le 2.0$ mA (Figures 1, 2)	2.0* 4 5 4.5 6.0	0.0 0.0 - 4.5 - 6.0	- 160 90 90	- 200 110	- 240 130 130	Ω
	WWW .	$V_{ir} = V_{IH}$ $v_{IS} = v_{CC}$ or $V_{EE}$ (Endpoints) $I_{S} \le 2.0$ mA (Figures 1, 2)	2 0 4.5 4.5 6.0	0.0 - 4.5 - 6.0	- 90 70 70	- 115 90 90	- 140 105 105	
ΔR <sub>on</sub>	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{aligned} &V_{in} = V_{IH} \\ &V_{IS} = 1/2 \; (V_{CC} - V_{EE}) \\ &I_{S} \leq 2.0 \; \text{mA} \end{aligned}$	2.0 4.5 4.5 6.0	0.0 0.0 - 4.5 - 6.0	- 20 15 15	- 25 20 20	- 30 25 25	Ω
l <sub>off</sub>	Maximum Off-Channel Leakage Current, Any One Channel	$V_{in} = V_{IL}$ $V_{IO} = V_{CC}$ or $V_{EE}$ Switch Off (Figure 3)	6.0	- 6.0	0.1	0.5	1.0	μΑ
I <sub>on</sub>	Maximum On-Channel Leakage Current, Any One Channel	$V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ or $V_{EE}$ (Figure 4)	6.0	- 6.0	0.1	0.5	1.0	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>\*</sup>At supply voltage (V<sub>CC</sub> - V<sub>EE</sub>) approaching 2.0 V the analog switch-on resistance becomes extremely non-linear. Therefore, for low-voltage operation, it is recommended that these devices only be used to control digital signals.

# $\textbf{AC ELECTRICAL CHARACTERISTICS} \ (C_L = 50 \ \text{pF}, \ \text{Control or Enable} \ t_r = t_f = 6 \ \text{ns}, \ V_{EE} = G \text{ND})$

			Gu	aranteed Li	mit	
Symbol	Parameter	v <sub>cc</sub> v	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Analog Input to Analog Output (Figures 8 and 9)	2.0 4.5 6.0	40 6 5	50 8 7	60 9 8	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Control or Enable to Analog Output (Figures 10 and 11)	2.0 4.5 6.0	130 40 30	160 50 40	200 60 50	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Control or Enable to Analog Output (Figures 10 and 11)	2.0 4.5 6.0	140 40 30	175 50 40	250 60 50	ns
С	Maximum Capacitance ON/OFF Control and Enable Inputs	-	10	10	10	pF
	Control Input = GND Analog I/O Feedthrough	-	35 1.0	35 1.0	35 1.0	

<sup>1.</sup> For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>2.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

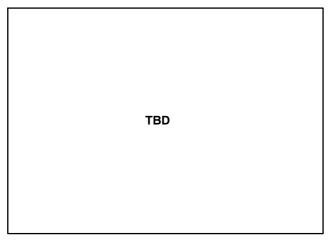
		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_PD$	Power Dissipation Capacitance (Per Switch) (Figure 13)*	15	pF

<sup>\*</sup>Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ . For load considerations, see Chapter 2of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	V <sub>EE</sub> V	Limit* 25°C	Unit
BW	Maximum On Channe Bandwidt or Minimum Frequency Response (Figure 5)	$t_{\rm in}$ = 1 MHz Sine Vav $\Theta$ at Vav $\Theta$ at Vav $\Theta$ locrease $\theta$ in Frequency until dB Meter Reads $-3$ dB $\Theta$ RL = 50 $\Omega$ , CL = 10 pF	2.25 4.50 6.00	-2.25 50 -6.00	150 160 160	MHz
-	Off–Channel Feedthrough Isolation (Figure 6)	$\begin{split} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_L = 600 \ \Omega, \text{ C}_L = 50 \text{ pF} \\ f_{in} &= 1.0 \text{ MHz}, \text{ R}_L = 50 \ \Omega, \text{ C}_L = 10 \text{ pF} \end{split}$	2.25 4.50 6.00 2.25 4.50 6.00	- 2.25 - 4.50 - 6.00 - 2.25 - 4.50 - 6.00	- 50 - 50 - 50 - 40 - 40 - 40	dB
-	Feedthrough Noise, Control to Switch (Figure 7)	$\begin{split} V_{in} & \leq \text{ 1 MHz Square Wave } (t_r = t_f = 6 \text{ ns}) \\ \text{Adjust } R_L \text{ at Setup so that } I_S = 0 \text{ A} \\ R_L & = 600 \ \Omega, \ C_L = 50 \text{ pF} \\ R_L & = 10 \text{ k}\Omega, \ C_L = 10 \text{ pF} \end{split}$	2.25 4.50 6.00 2.25 4.50 6.00	- 2.25 - 4.50 - 6.00 - 2.25 - 4.50 - 6.00	60 130 200 30 65 100	mV <sub>PP</sub>
-	Crosstalk Between Any Two Switches (Figure 12)	$\begin{split} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} \text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_L = 600 \ \Omega, \text{ C}_L = 50 \text{ pF} \\ f_{in} &= 1.0 \text{ MHz}, \text{ R}_L = 50 \ \Omega, \text{ C}_L = 10 \text{ pF} \end{split}$	2.25 4.50 6.00 2.25 4.50 6.00	- 2.25 - 4.50 - 6.00 - 2.25 - 4.50 - 6.00	- 70 - 70 - 70 - 80 - 80 - 80	dΒ
THD	Total Harmonic Distortion (Figure 14)	$\begin{split} f_{in} = 1 \text{ kHz, } R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF} \\ \text{THD} = \text{THD}_{Measured} - \text{THD}_{Source} \\ V_{IS} = 4.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 8.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 11.0 \text{ V}_{PP} \text{ sine wave} \end{split}$	2.25 4.50 6.00	- 2.25 - 4.50 - 6.00	0.10 0.06 0.04	%

<sup>\*</sup>Limits not tested. Determined by design and verified by qualification.



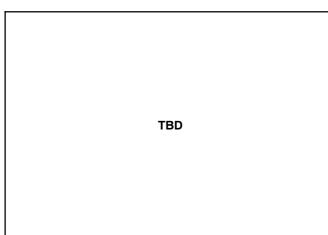


Figure 1a. Typical On Resistance,  $V_{CC} - V_{EE} = 2.0 \text{ V}$ 

Figure 1b. Typical On Resistance,  $V_{CC} - V_{EE} = 4.5 \text{ V}$ 

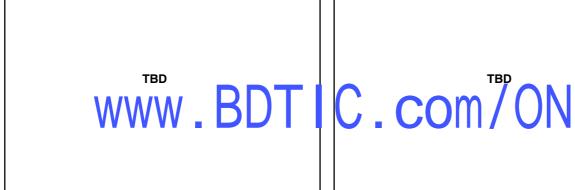




Figure 1c. Typical On Resistance,  $V_{CC} - V_{EE} = 6.0 V$ 

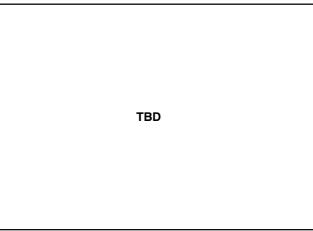
Figure 1d. Typical On Resistance,  $V_{CC} - V_{EE} = 9.0 V$ 

**PLOTTER** 

MINI COMPUTER

**DEVICE UNDER TEST**  DC ANALYZER

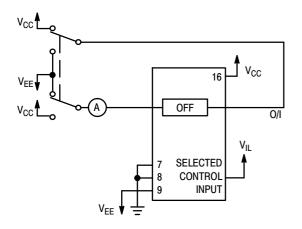
V<sub>CC</sub>



ANALOG IN COMMON OUT GND  $V_{EE}$ Figure 1e. Typical On Resistance, Figure 2. On Resistance Test Set-Up  $V_{CC} - V_{EE} = 12.0 \text{ V}$ 

**PROGRAMMABLE** 

**POWER** SUPPLY



V<sub>CC</sub>

A

ON

N/C

V<sub>EE</sub>

7

SELECTED
8

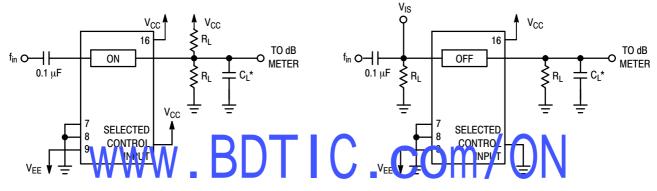
CONTROL
9

INPUT

VIH

Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

Figure 4. Maximum On Channel Leakage Current, Test Set-Up



<sup>\*</sup>Includes all probe and jig capacitance.

Figure 5. Maximum On-Channel Bandwidth Test Set-Up

\*Includes all probe and jig capacitance.

Figure 6. Off-Channel Feedthrough Isolation, Test Set-Up

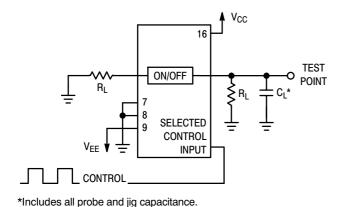


Figure 7. Feedthrough Noise, Control to Analog Out, Test Set-Up

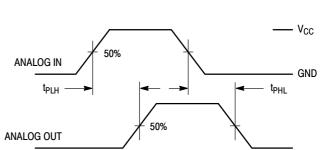
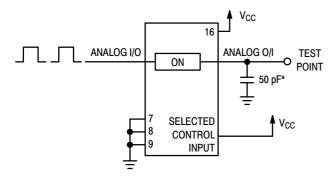


Figure 8. Propagation Delays, Analog In to Analog Out



\*Includes all probe and jig capacitance.

Figure 9. Propagation Delay Test Set-Up

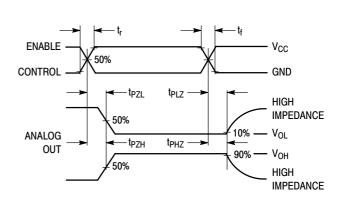
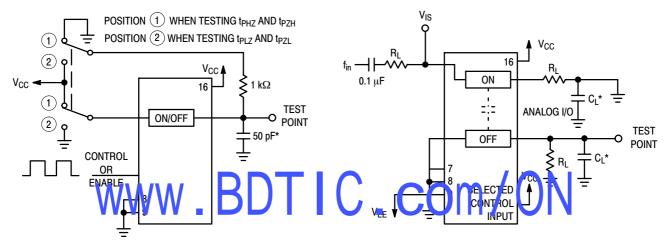


Figure 10. Propagation Delay, ON/OFF Control to Analog Out



\*Includes all probe and jig capacitance.

Figure 11. Propagation Delay Test Set-Up

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up (Adjacent Channels Used)

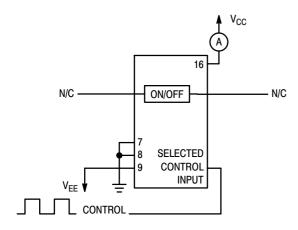
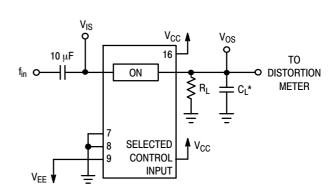


Figure 13. Power Dissipation Capacitance
Test Set-Up



\*Includes all probe and jig capacitance.

Figure 14. Total Harmonic Distortion, Test Set-Up

<sup>\*</sup>Includes all probe and jig capacitance.

#### **APPLICATIONS INFORMATION**

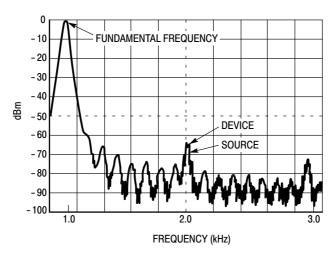


Figure 15. Plot, Harmonic Distortion

The Enable and Control pins should be at  $V_{CC}$  or GND logic levels,  $V_{CC}$  being recognized as logic high and GND being recognized as a logic low. Unused analog inputs/outputs may be left floating (not connected). However, it is advisable to tie unused analog inputs and outputs to  $V_{CC}$  or  $V_{EE}$  through a low value resistor. This minimizes crosstalk and feedthrough noise that may be picked up by the unused I/O pins.

The maximum analog voltage swings are determined by the supply voltages  $V_{CC}$  and  $V_{CE}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the legitive peak analog voltage should not go below  $V_{EE}$ . In the example below, the difference between  $V_{CC}$  and  $V_{EE}$  is 12 V.

Therefore, using the configuration in Figure 16, a maximum analog signal of twelve volts peak-to-peak can be controlled.

When voltage transients above  $V_{CC}$  and/or below  $V_{EE}$  are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure 17. These diodes should be small signal, fast turn-on types able to absorb the maximum anticipated current surges during clipping. An alternate method would be to replace the Dx diodes with MOSORDs (MOSORD) is an acronyn for high current surge protectors). MOSORBs are last turn-on devices ideally suited for precise de protection with no inherent wear out mechanism.

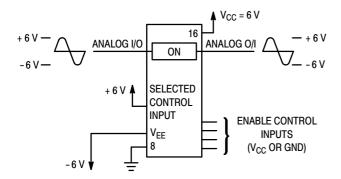


Figure 16.

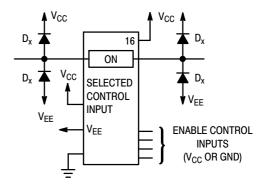


Figure 17. Transient Suppressor Application

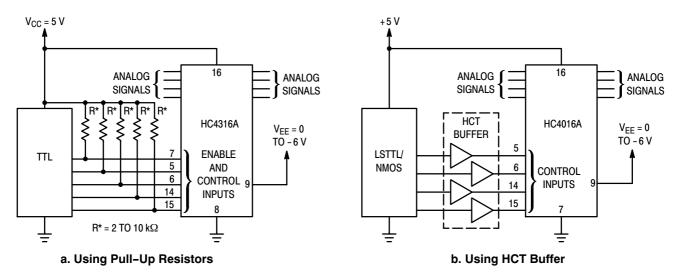


Figure 18. LSTTL/NMOS to HCMOS Interface

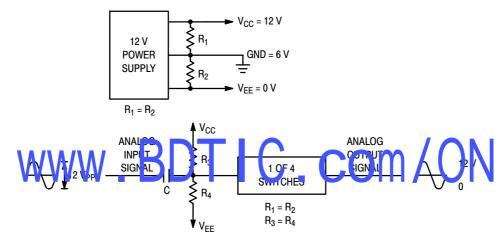


Figure 19. Switching a 0-to-12 V Signal Using a Single Power Supply (GND  $\neq$  0 V)

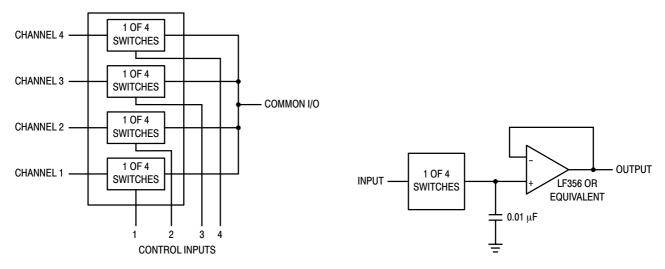
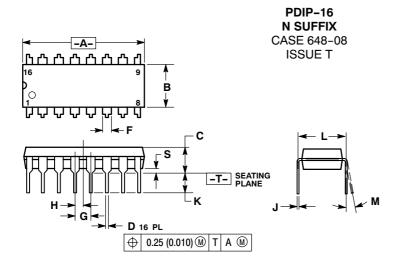


Figure 20. 4-Input Multiplexer

Figure 21. Sample/Hold Amplifier

#### PACKAGE DIMENSIONS



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

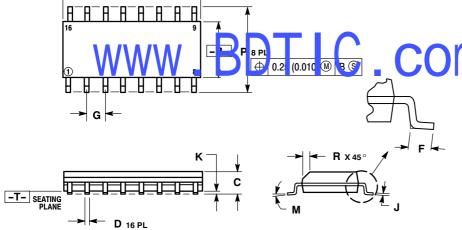
  4. DIMENSION B DOES NOT INCLUDE MODE I ASH

- MOLD FLASH.

  5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100 BSC		2.54	BSC	
Н	0.050 BSC		1.27	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
М	0°	10 °	0°	10 °	
S	0.020	0.040	0.51	1.01	





⊕ 0.25 (0.010) M T B S A S

-A-

#### NOTES:

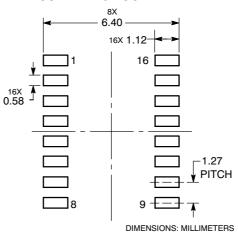
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTPUSION.

  MAXIM JM N OLD RC RUS ON 0.15 (0.00 PER 5 DE. RUS ON 0.15 (0.006)
  - PINE AUST.

    JUNE ASSON D DOLS TO AN CLUDE DAMBAR
    PROTRUSION SHALL BE 0.127 (0.005) TOTAL
    IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

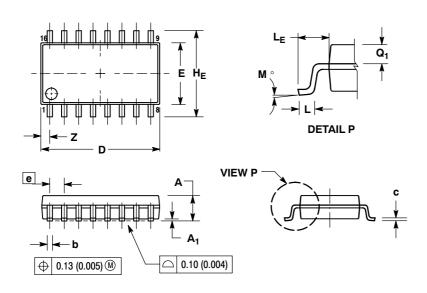
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	1.27 BSC		BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019





#### PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE A** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT, MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018)

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A <sub>1</sub>	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.10	0.20	0.007	0.011	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27 BSC		0.050	BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10°	
$Q_1$	0.70	0.90	0.028	0.035	
Z		0.78		0.031	

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